

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | | | Symbol | Value | Unit |
|---|--------------|--|------------------|----------------|------|
| Drain-Source Voltage | | | V _{DSS} | -30 | V |
| Gate-Source Voltage | | | V _{GSS} | ±20 | V |
| Continuous Drain Current (Note 7) V _{GS} = -10V | Steady State | T _A = +25°C T _A = +70°C | I _D | -36 -29 | A |
| Continuous Drain Current (Note 7) V _{GS} = -4.5V | Steady State | T _A = +25°C T _A = +70°C | I _D | -31 -25 | A |
| Continuous Drain Current (Note 6) V _{GS} = -10V | Steady State | T _A = +25°C T _A = +70°C | I _D | -14.5 -11.5 | A |
| Pulsed Drain Current (Notes 6 & 9) | | | I _{DM} | -100 | A |
| Avalanche Current (Notes 10 & 11) | | | I _{AS} | -17.5 | A |
| Avalanche Energy (Notes 10 & 11) L = 1mH | | | E _{AS} | 153 | mJ |

Thermal Characteristics

| Characteristic | Symbol | Value | Unit |
|--|-----------------------------------|-------------|------|
| Power Dissipation (Note 5) | P _D | 1.26 | W |
| Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5) | R _{θJA} | 97 | °C/W |
| Power Dissipation (Note 6) | P _D | 2.18 | W |
| Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 6) | R _{θJA} | 55 | °C/W |
| Power Dissipation (Note 7) | P _D | 14.37 | W |
| Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 7) | R _{θJA} | 8.7 | °C/W |
| Power Dissipation (Notes 7 & 8) | P _D | 58.7 | W |
| Thermal Resistance, Junction to Case @T _C = +25°C (Notes 7 & 8) | R _{θJC} | 2.13 | °C/W |
| Operating and Storage Temperature Range | T _J , T _{STG} | -55 to +150 | °C |

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|---|---------------------|------|-------|------|------|---|
| OFF CHARACTERISTICS (Note 11) | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | -30 | — | — | V | V _{GS} = 0V, I _D = -250μA |
| Zero Gate Voltage Drain Current | I _{DSS} | — | — | -1.0 | μA | V _{DS} = -30V, V _{GS} = 0V |
| Gate-Source Leakage | I _{GSS} | — | — | ±100 | nA | V _{GS} = ±20V, V _{DS} = 0V |
| ON CHARACTERISTICS (Note 11) | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | -1.1 | -1.6 | -2.1 | V | V _{DS} = V _{GS} , I _D = -250μA |
| Static Drain-Source On-Resistance | R _{DS(ON)} | — | 5.7 | 7.5 | mΩ | V _{GS} = -10V, I _D = -10A |
| | | — | 7.2 | 10 | | V _{GS} = -4.5V, I _D = -10A |
| Forward Transfer Admittance | Y _{fs} | — | 30 | — | S | V _{DS} = -15V, I _D = -10A |
| Diode Forward Voltage | V _{SD} | — | -0.65 | -1.0 | V | V _{GS} = 0V, I _S = -1A |
| DYNAMIC CHARACTERISTICS (Note 12) | | | | | | |
| Input Capacitance | C _{iss} | — | 6,234 | — | pF | V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz |
| Output Capacitance | C _{oss} | — | 1,500 | — | pF | |
| Reverse Transfer Capacitance | C _{rss} | — | 774 | — | pF | |
| Gate Resistance | R _g | — | 1.28 | — | Ω | V _{DS} = 0V, V _{GS} = 0V, f = 1MHz |
| Total Gate Charge (V _{GS} = -10V) | Q _g | — | 126.2 | — | nC | V _{DS} = -15V, I _D = -10A |
| Total Gate Charge (V _{GS} = -4.5V) | Q _g | — | 59.2 | — | nC | |
| Gate-Source Charge | Q _{gs} | — | 16.1 | — | nC | |
| Gate-Drain Charge | Q _{gd} | — | 15.7 | — | nC | |
| Turn-On Delay Time | t _{D(ON)} | — | 11.4 | — | ns | V _{DS} = -15V, V _{GEN} = -10V, R _G = 6Ω, I _D = -1A |
| Turn-On Rise Time | t _r | — | 9.4 | — | ns | |
| Turn-Off Delay Time | t _{D(OFF)} | — | 260.7 | — | ns | |
| Turn-Off Fall Time | t _f | — | 99.3 | — | ns | |

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - Device mounted on FR-4 PCB with infinite heatsink.
 - R_{θJC} is guaranteed by design while R_{θCA} is determined by the user's board design.
 - Repetitive rating, pulse width limited by junction temperature, 10s pulse, duty cycle = 1%.
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

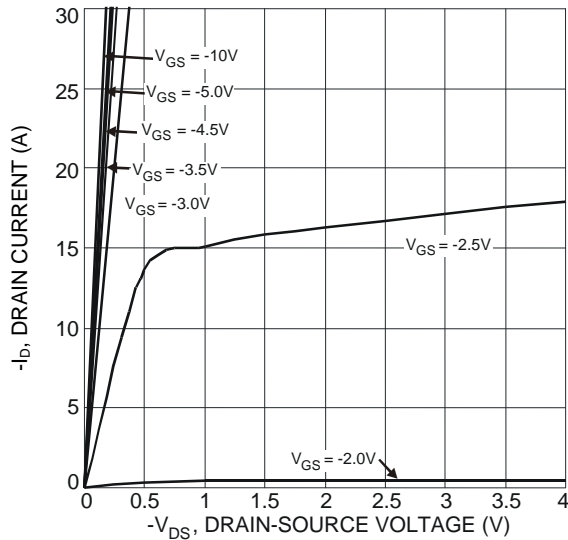


Fig. 1 Typical Output Characteristic

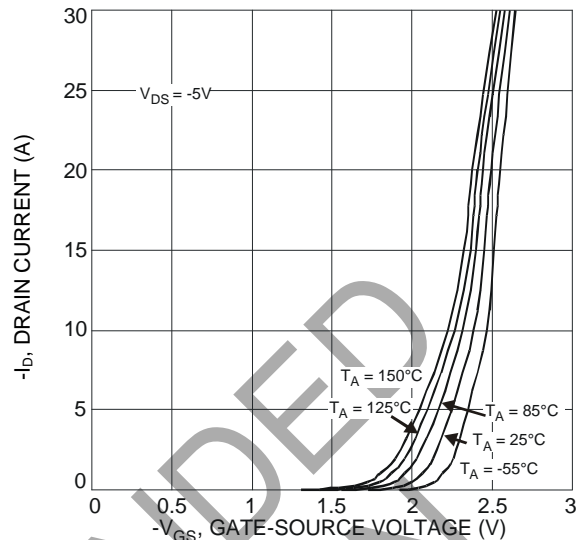


Fig. 2 Typical Transfer Characteristic

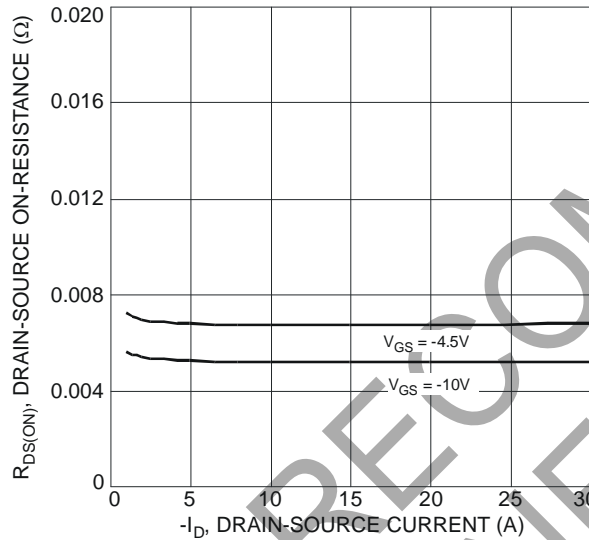


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

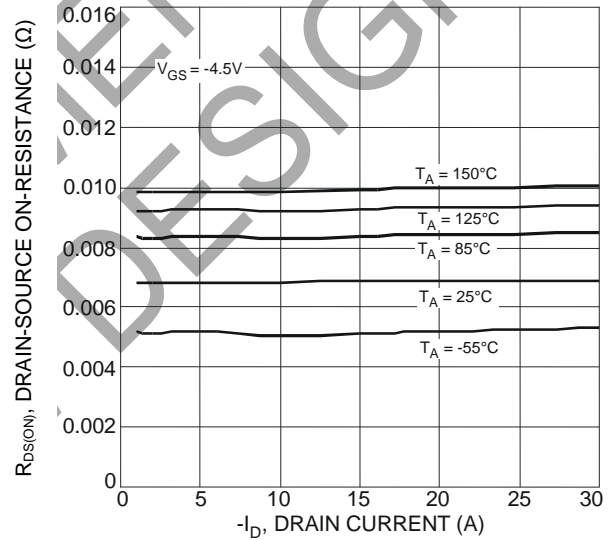


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

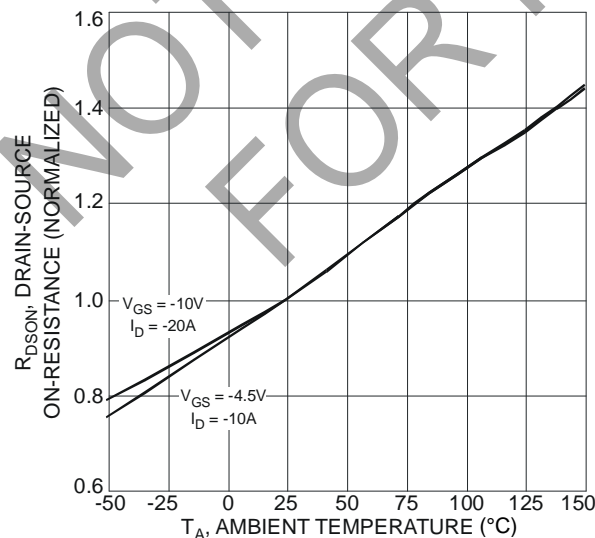


Fig. 5 On-Resistance Variation with Temperature

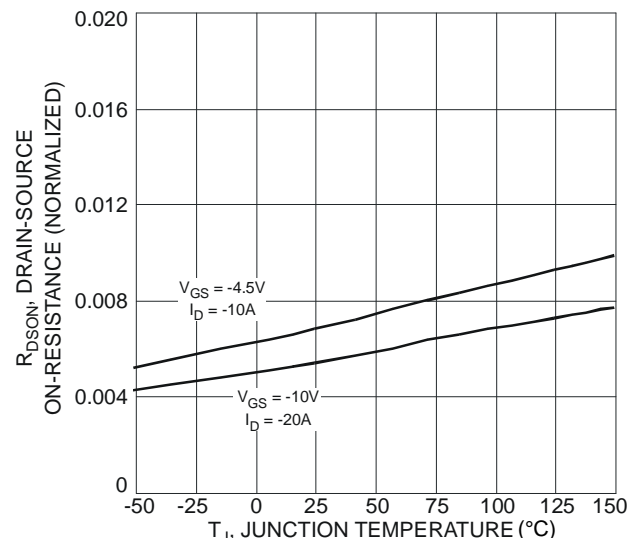


Fig. 6 On-Resistance Variation with Temperature

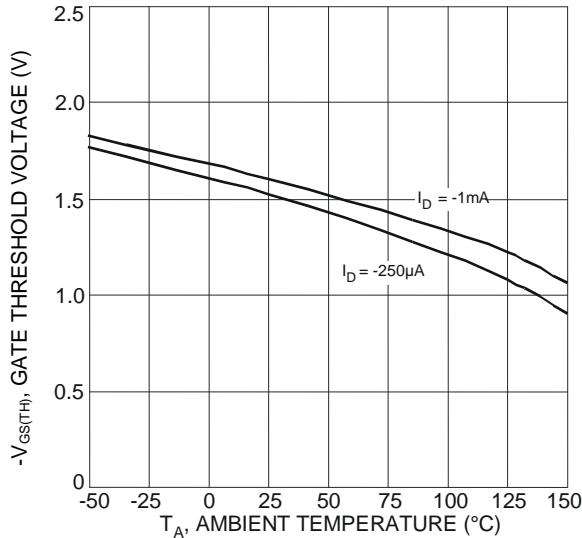


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

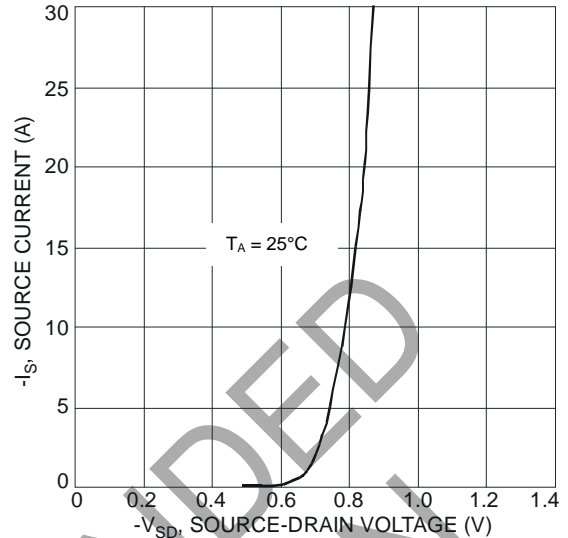


Fig. 8 Diode Forward Voltage vs. Current

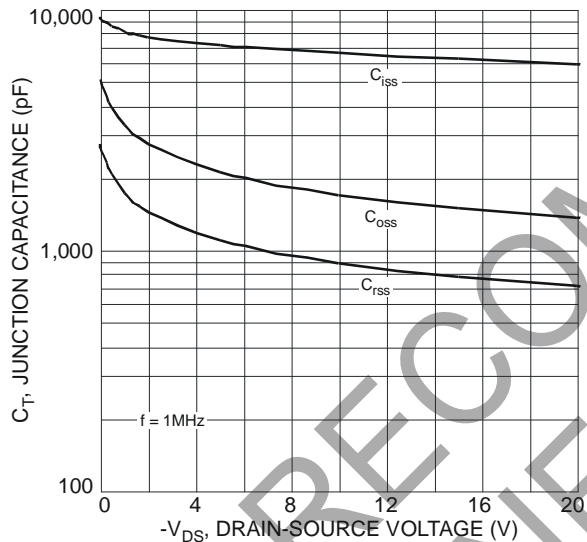


Fig. 9 Typical Total Capacitance

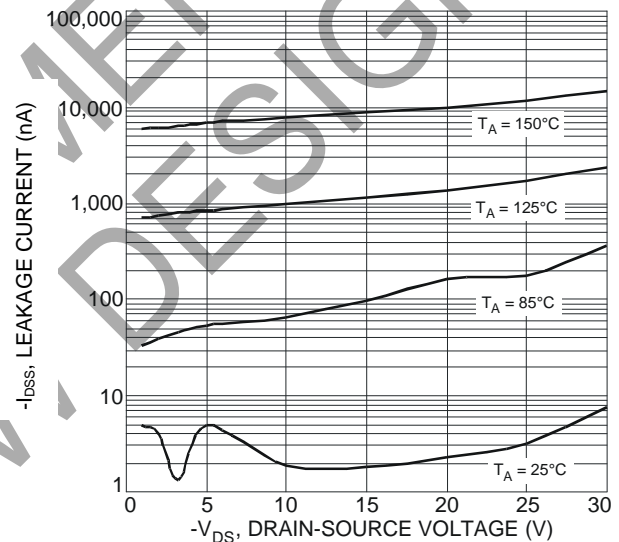


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

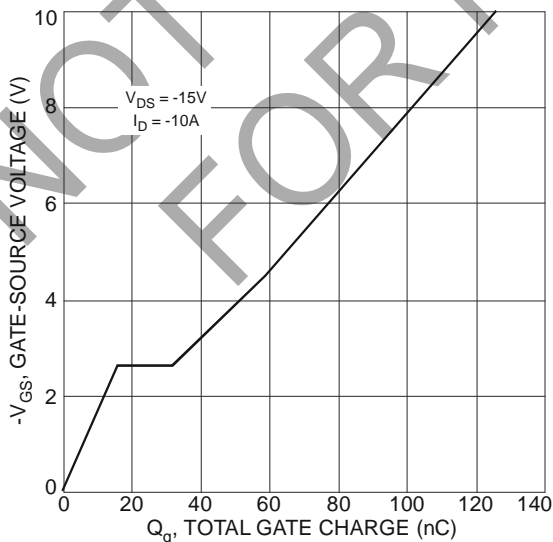


Fig. 11 Gate-Source Voltage vs. Total Gate Charge

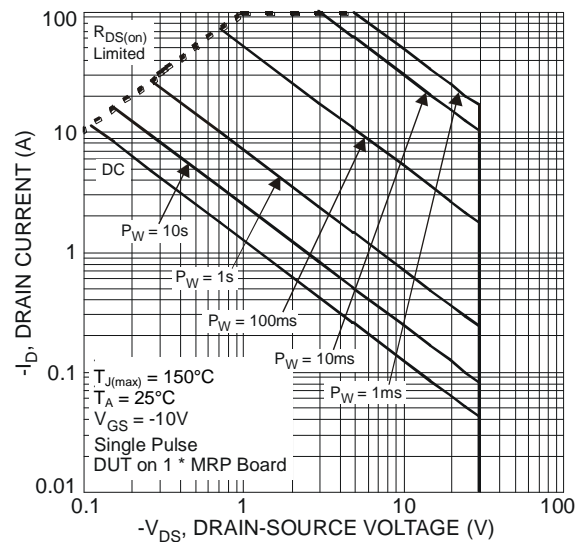


Fig. 12 SOA, Safe Operation Area

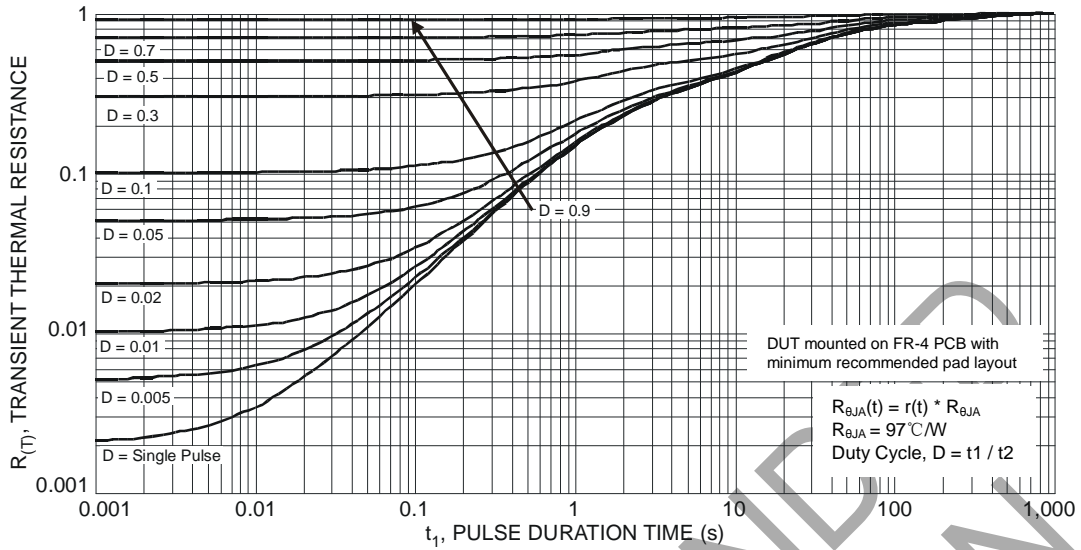
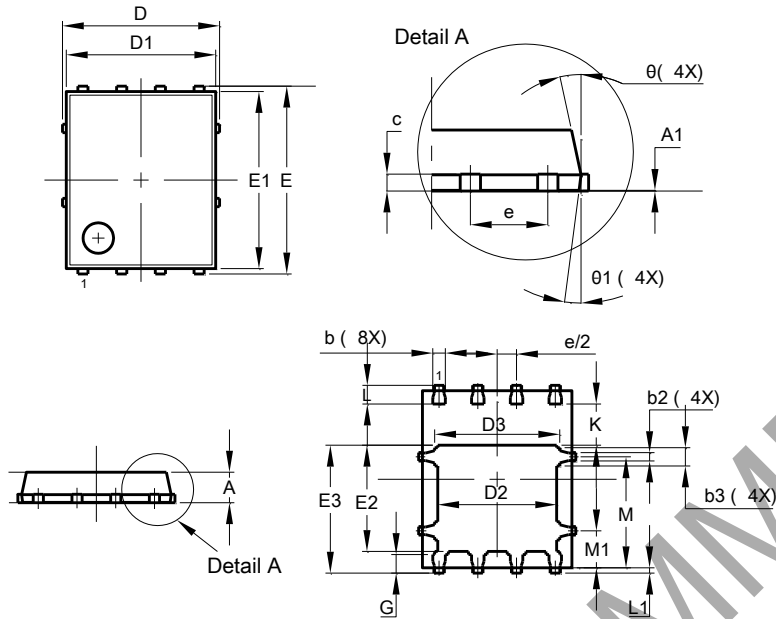


Fig. 13 Transient Thermal Response

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8

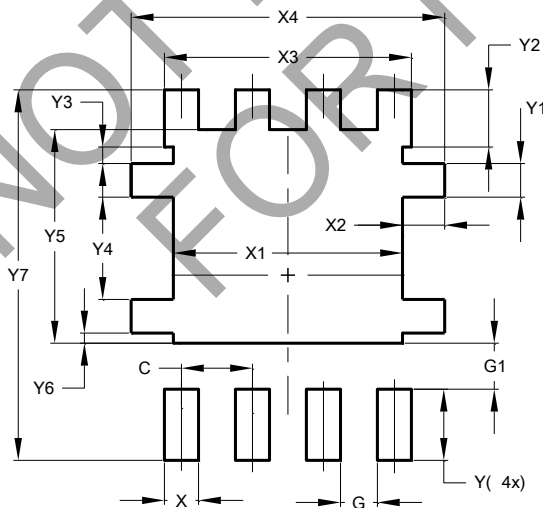


| PowerDI5060-8 | | | |
|----------------------|----------|-------|-------|
| Dim | Min | Max | Typ |
| A | 0.90 | 1.10 | 1.00 |
| A1 | 0.00 | 0.05 | — |
| b | 0.33 | 0.51 | 0.41 |
| b2 | 0.200 | 0.350 | 0.273 |
| b3 | 0.40 | 0.80 | 0.60 |
| c | 0.230 | 0.330 | 0.277 |
| D | 5.15 BSC | | |
| D1 | 4.70 | 5.10 | 4.90 |
| D2 | 3.70 | 4.10 | 3.90 |
| D3 | 3.90 | 4.30 | 4.10 |
| E | 6.15 BSC | | |
| E1 | 5.60 | 6.00 | 5.80 |
| E2 | 3.28 | 3.68 | 3.48 |
| E3 | 3.99 | 4.39 | 4.19 |
| e | 1.27 BSC | | |
| G | 0.51 | 0.71 | 0.61 |
| K | 0.51 | — | — |
| L | 0.51 | 0.71 | 0.61 |
| L1 | 0.100 | 0.200 | 0.175 |
| M | 3.235 | 4.035 | 3.635 |
| M1 | 1.00 | 1.40 | 1.21 |
| θ | 10° | 12° | 11° |
| θ_1 | 6° | 8° | 7° |
| All Dimensions in mm | | | |

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8



| Dimensions | Value (in mm) |
|------------|---------------|
| C | 1.270 |
| G | 0.660 |
| G1 | 0.820 |
| X | 0.610 |
| X1 | 4.100 |
| X2 | 0.755 |
| X3 | 4.420 |
| X4 | 5.610 |
| Y | 1.270 |
| Y1 | 0.600 |
| Y2 | 1.020 |
| Y3 | 0.295 |
| Y4 | 1.825 |
| Y5 | 3.810 |
| Y6 | 0.180 |
| Y7 | 6.610 |

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